

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type (PCT process)

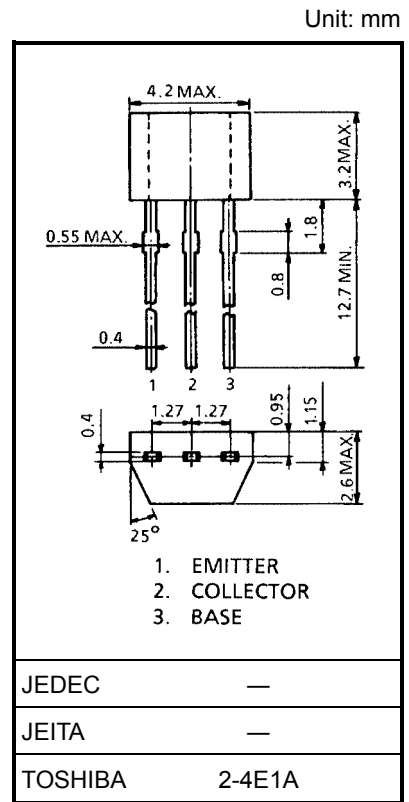
2SC2668

High Frequency Amplifier Applications
 FM, RF, IF Amplifier Applications

- Small reverse transfer capacitance: $C_{re} = 0.70$ pF (typ.)
- Low noise figure: NF = 2.5dB (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	40	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	4	V
Collector current	I_C	20	mA
Emitter current	I_B	4	mA
Collector power dissipation	P_C	100	mW
Junction temperature range	T_j	125	°C
Storage temperature range	T_{stg}	-55~125	°C

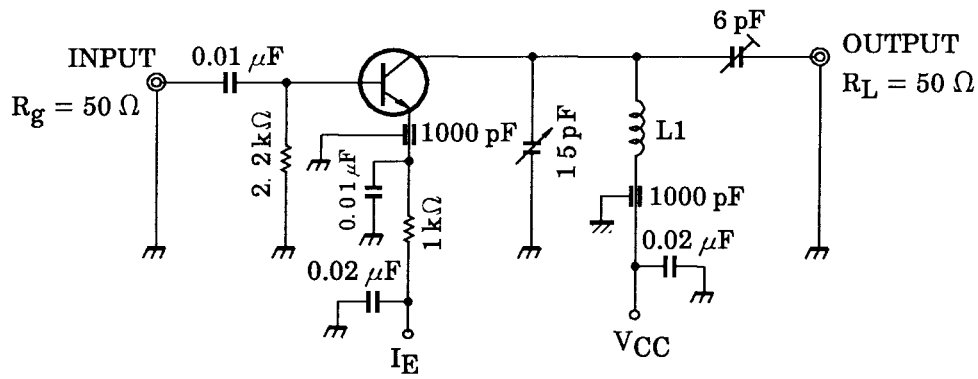


Weight: 0.13 g (typ.)

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 40$ V, $I_E = 0$	—	—	0.5	μ A
Emitter cut-off current	I_{EBO}	$V_{EB} = 4$ V, $I_C = 0$	—	—	0.5	μ A
DC current gain	h_{FE} (Note)	$V_{CE} = 6$ V, $I_C = 1$ mA	40	—	200	
Reverse transfer capacitance	C_{re}	$V_{CE} = 6$ V, $f = 1$ MHz	—	0.70	—	pF
Transition frequency	f_T	$V_{CE} = 6$ V, $I_C = 1$ mA	—	550	—	MHz
Collector-base time constant	$C_c \cdot r_{bb'}$	$V_{CE} = 6$ V, $I_E = -1$ mA, $f = 30$ MHz	—	—	30	ps
Noise figure	NF	$V_{CC} = 6$ V, $I_E = -1$ mA, $f = 100$ MHz, (Figure 1)	—	2.5	5.0	dB
Power gain	G_{pe}		—	18	—	dB

Note: h_{FE} classification R: 40~80 O: 70~140 Y: 100~200



L₁: 0.8 mmφ silver plated copper wire, 4 turns. 10 mm ID, 8 mm length.

Figure 1 NF, G_{pe} Test Circuit

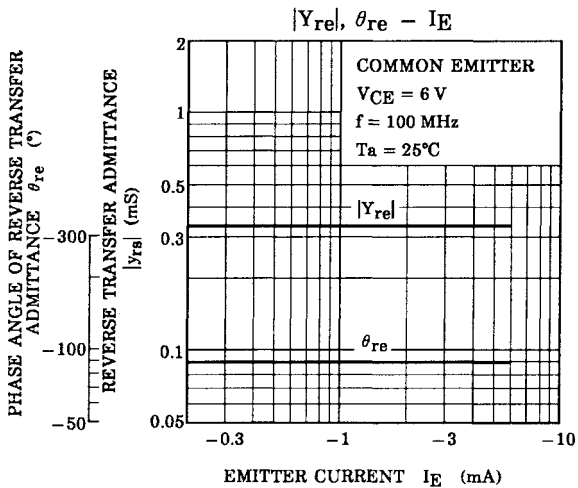
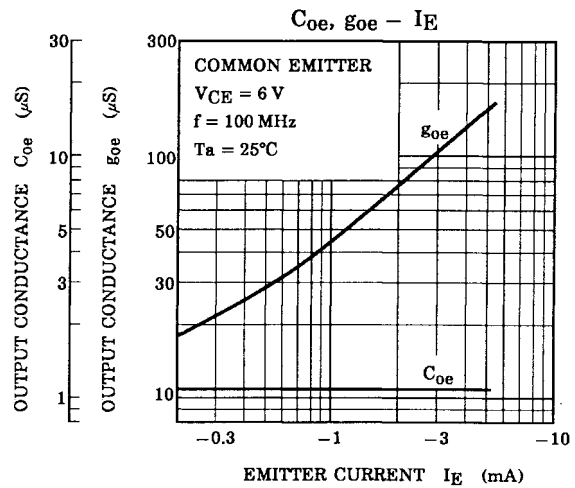
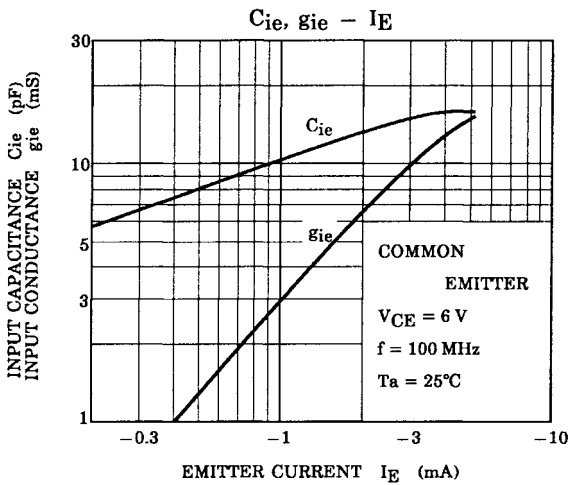
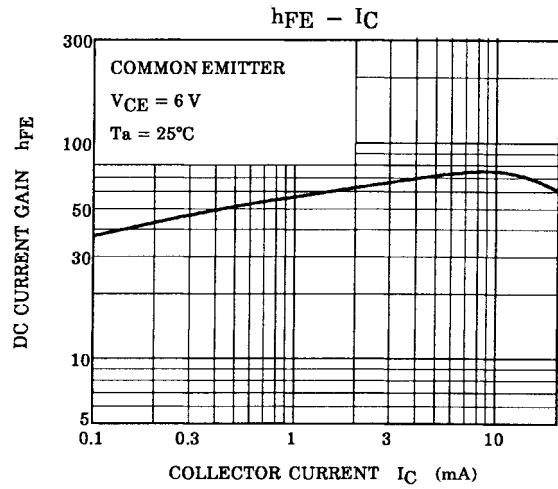
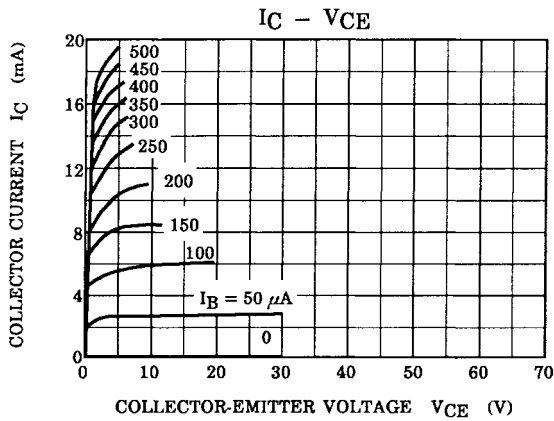
Y Parameter (typ.)

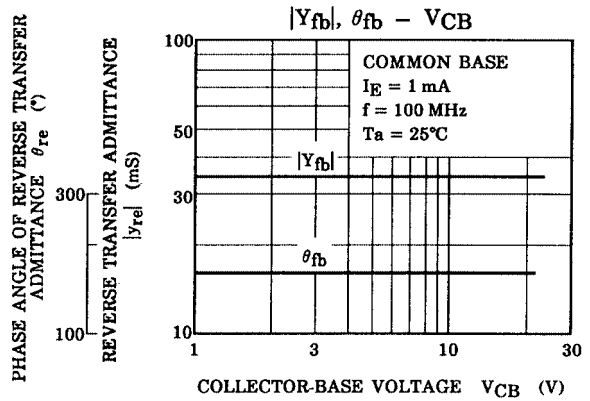
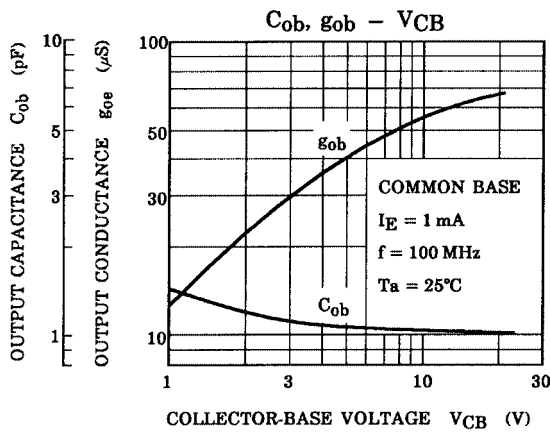
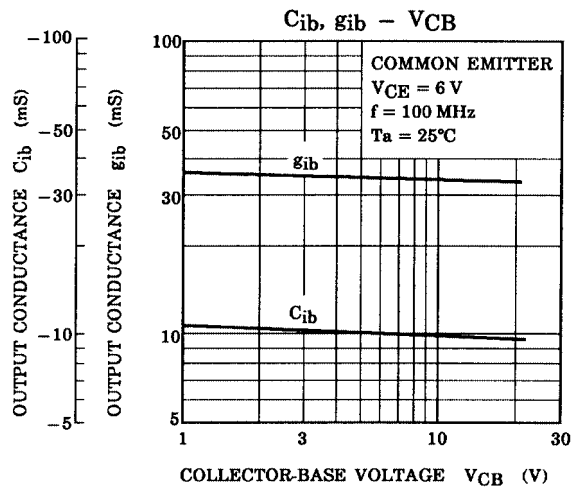
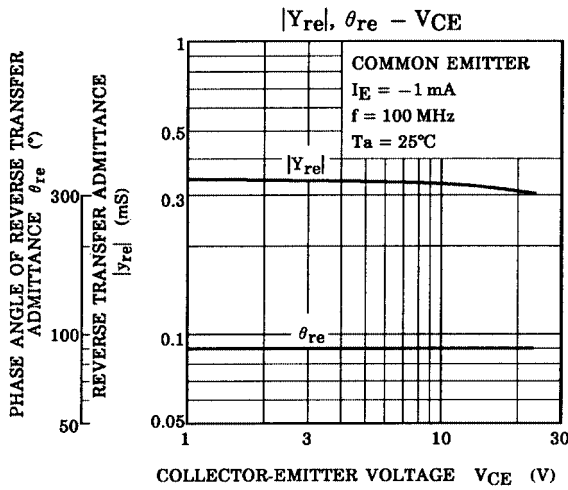
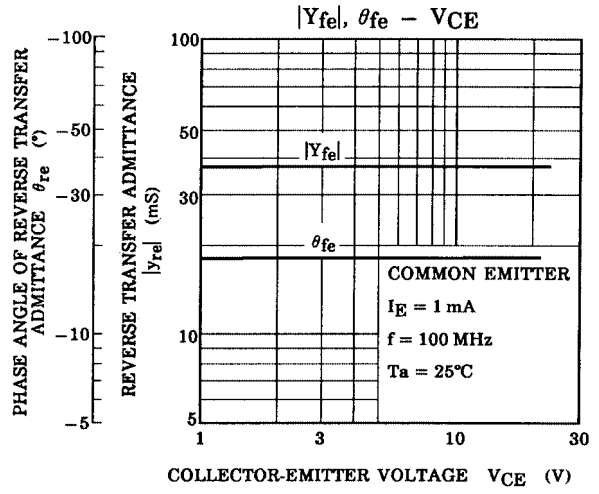
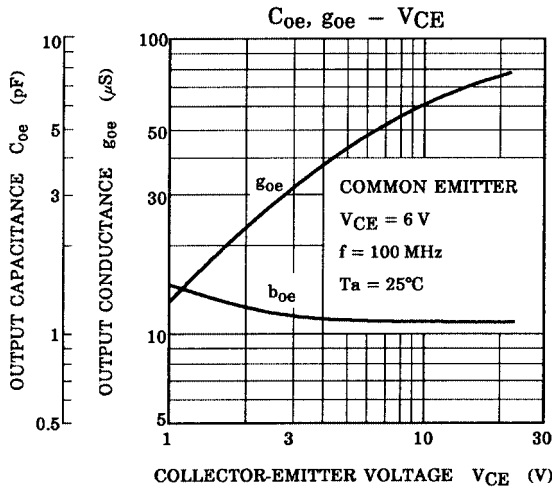
- (1) Common emitter (V_{CE} = 6 V, I_E = -1 mA, f = 100 MHz)

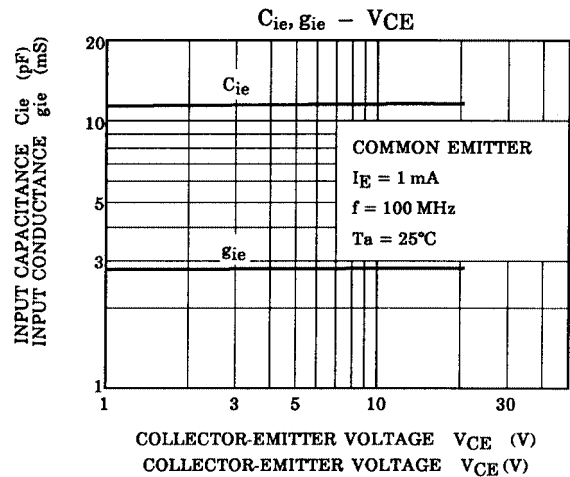
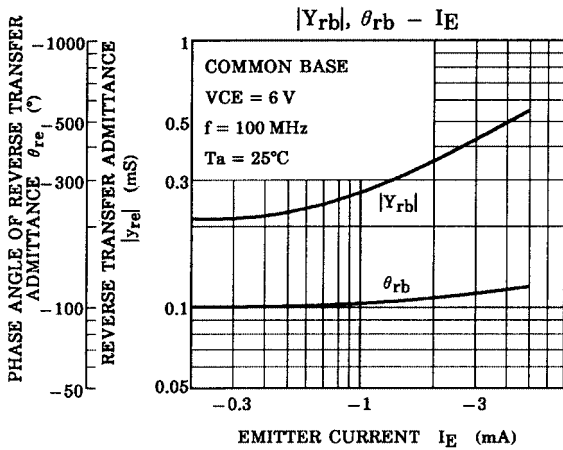
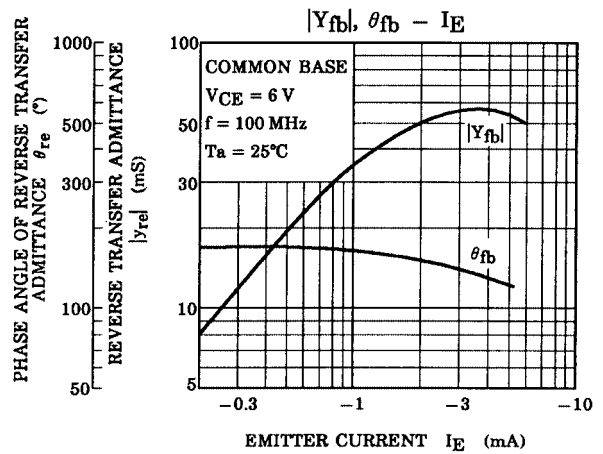
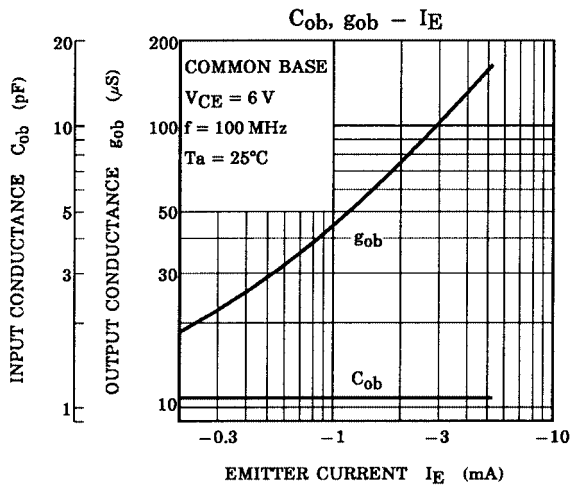
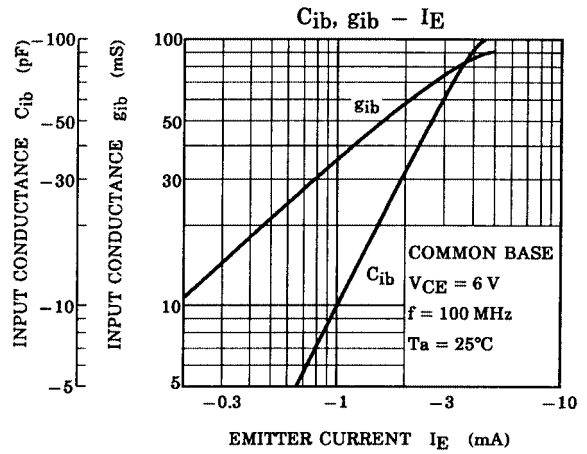
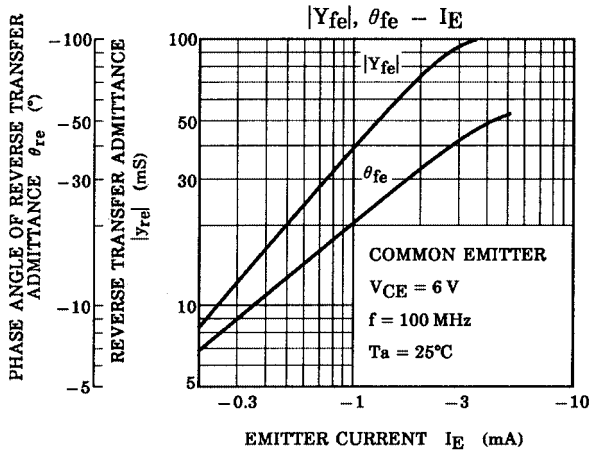
Characteristics	Symbol	Typ.	Unit
Input conductance	g _{ie}	2.9	ms
Input capacitance	C _{ie}	10.2	pF
Reverse transfer admittance	Y _{re}	0.33	ms
Phase angle of reverse transfer admittance	θ _{re}	-90	°
Forward transfer admittance	Y _{fe}	40	ms
Phase angle of forward transfer admittance	θ _{fe}	-20	°
Output conductance	g _{oe}	45	μs
Output capacitance	C _{oe}	1.1	pF

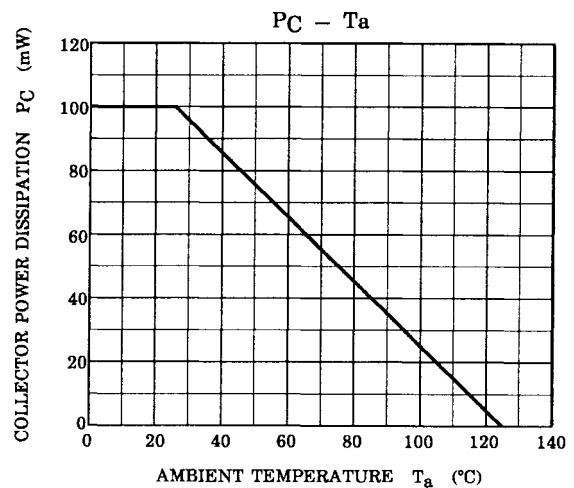
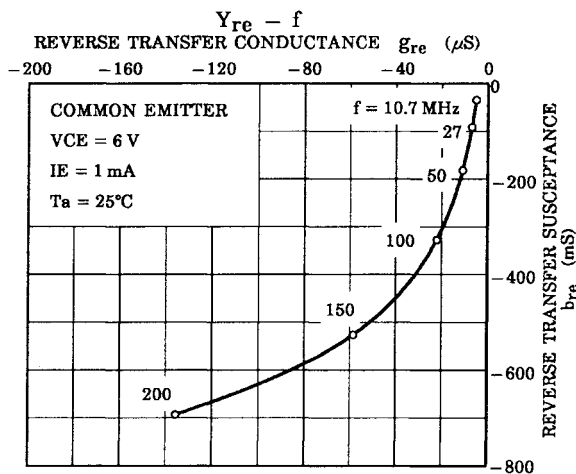
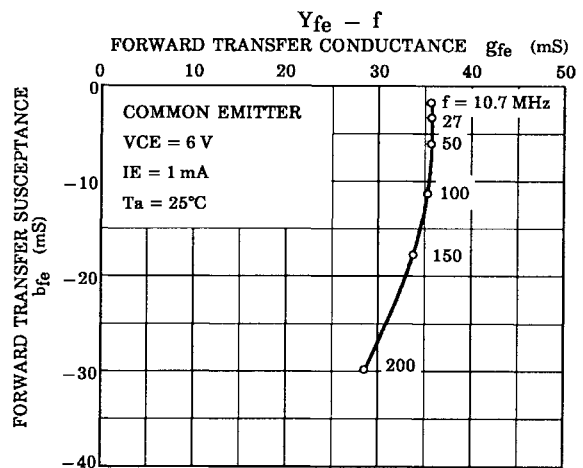
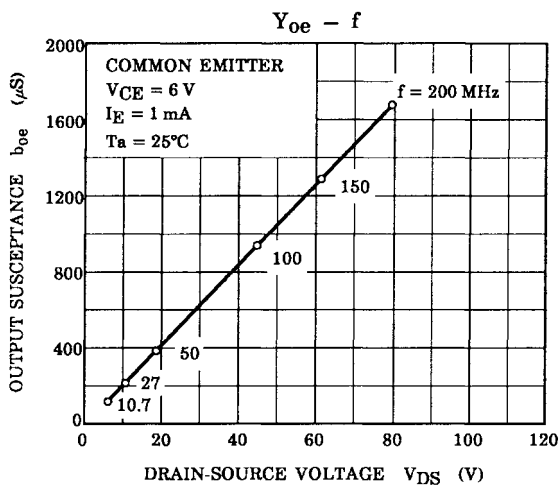
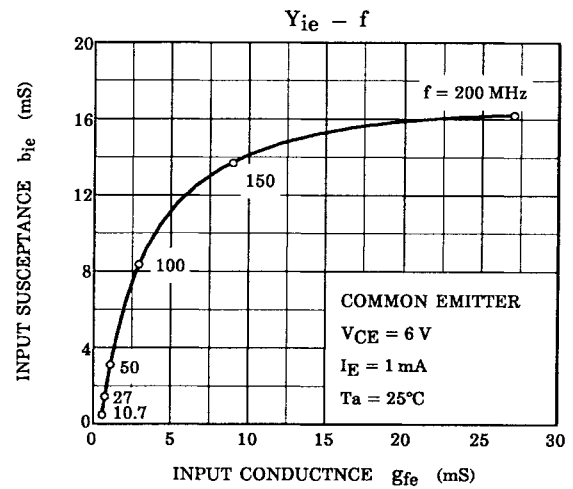
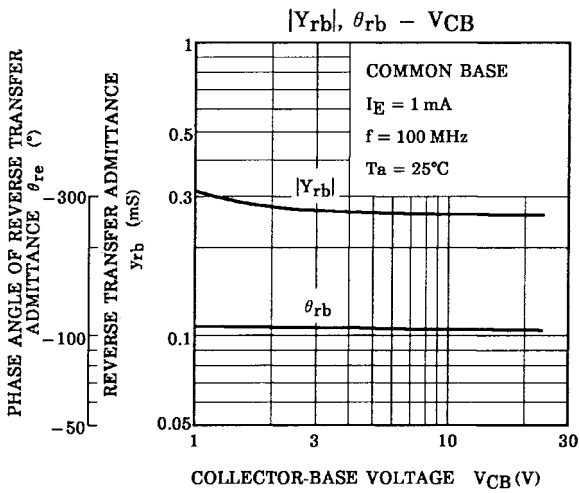
- (2) Common base (V_{CB} = 6 V, I_E = -1 mA, f = 100 MHz)

Characteristics	Symbol	Typ.	Unit
Input conductance	g _{ib}	34	ms
Input capacitance	C _{ib}	-10	pF
Reverse transfer admittance	Y _{rb}	0.27	ms
Phase angle of reverse transfer admittance	θ _{rb}	-105	°
Forward transfer admittance	Y _{fb}	34	ms
Phase angle of forward transfer admittance	θ _{fb}	165	°
Output conductance	g _{ob}	45	μs
Output capacitance	C _{ob}	1.1	pF









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